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# 2SC5545

Silicon NPN Epitaxial  
VHF / UHF wide band amplifier

## HITACHI

ADE-208-746 (Z)  
1st. Edition  
Jan. 1999

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### Features

- Excellent inter modulation characteristic
- High power gain and low noise figure ;  
PG=16dB typ. , NF=1.1dB typ. at f=900MHz

### Outline

MPAK-4



1. Collector
2. Emitter
3. Base
4. Emitter

Note: Marking is "ZS-".

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## 2SC5545

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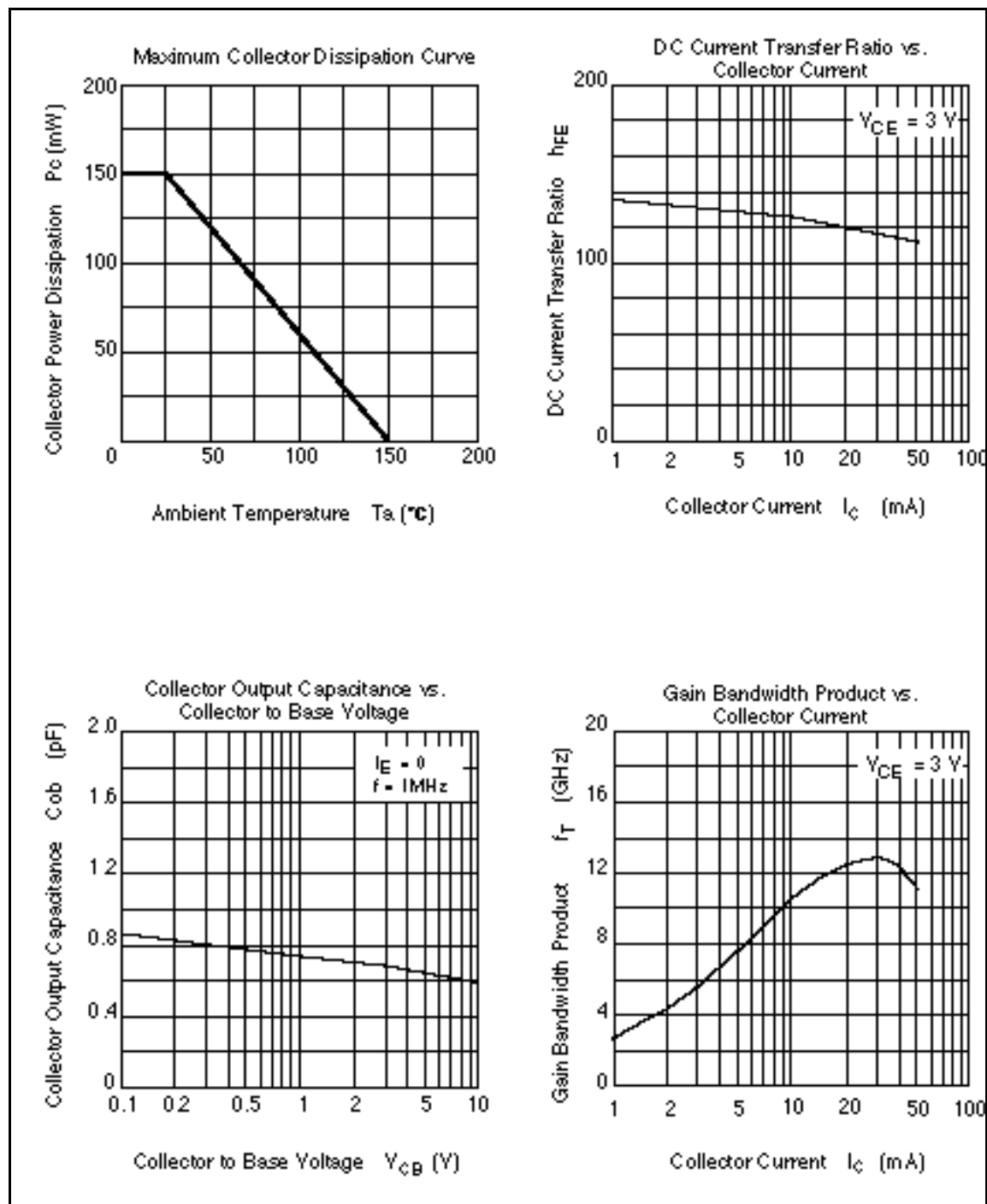
### Absolute Maximum Ratings (Ta = 25°C)

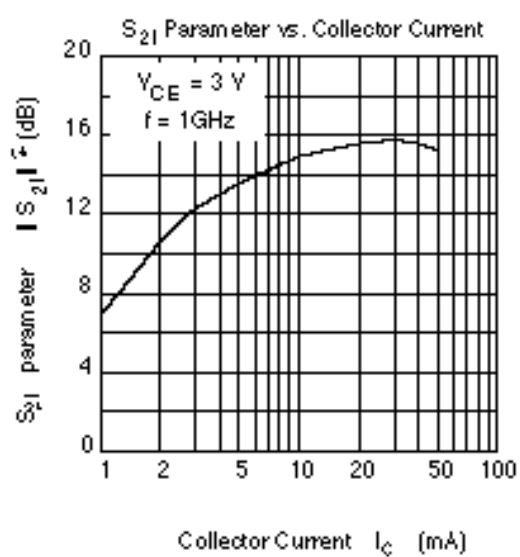
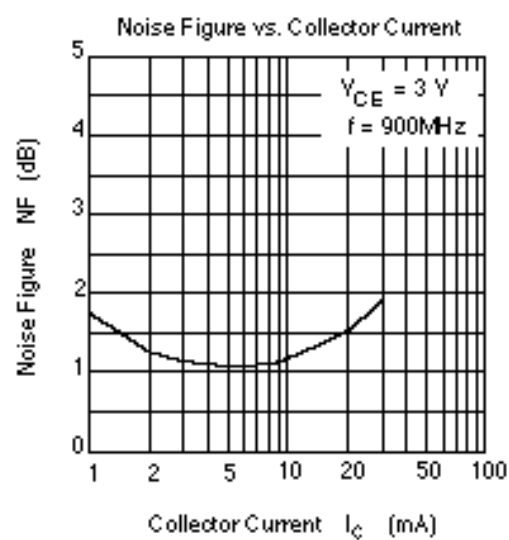
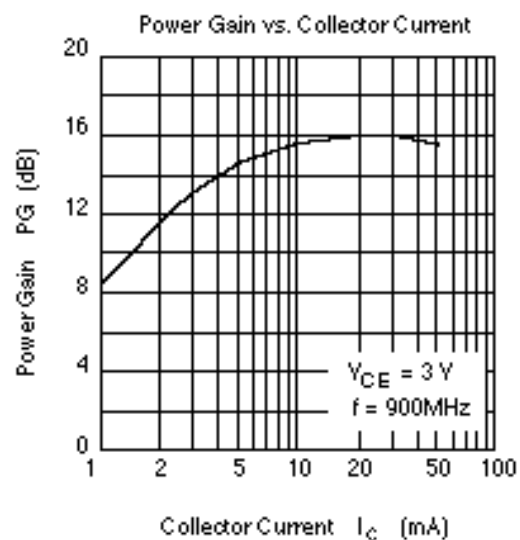
Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	15	V
Collector to emitter voltage	$V_{CEO}$	6	V
Emitter to base voltage	$V_{EBO}$	1.5	V
Collector current	$I_C$	50	mA
Collector power dissipation	$P_c$	150	mW
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

### Electrical Characteristics (Ta = 25°C)

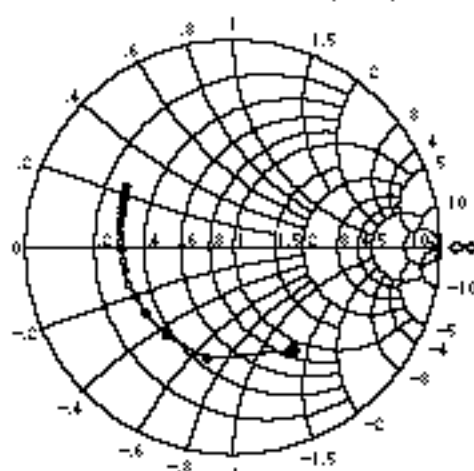
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	15	—	—	V	$I_C = 10\mu A$ , $I_E = 0$
Collector cutoff current	$I_{CBO}$	—	—	1	$\mu A$	$V_{CB} = 12V$ , $I_E = 0$
Collector cutoff current	$I_{CEO}$	—	—	1	mA	$V_{CE} = 6V$ , $R_{BE} =$
Emitter cutoff current	$I_{EBO}$	—	—	10	$\mu A$	$V_{EB} = 1.5V$ , $I_C = 0$
DC current transfer ratio	$h_{FE}$	80	120	160	V	$V_{CE} = 3V$ , $I_C = 20mA$
Collector output capacitance	$C_{ob}$	—	0.69	1.1	pF	$V_{CB} = 3V$ , $I_E = 0$ $f = 1MHz$
Gain bandwidth product	$f_T$	10	12.6	—	GHz	$V_{CE} = 3V$ , $I_C = 20mA$
Power gain	PG	14	16	—	dB	$V_{CE} = 3V$ , $I_C = 20mA$ $f = 900MHz$
Noise figure	NF	—	1.1	2.0	dB	$V_{CE} = 3V$ , $I_C = 5mA$ $f = 900MHz$

## Main Characteristics





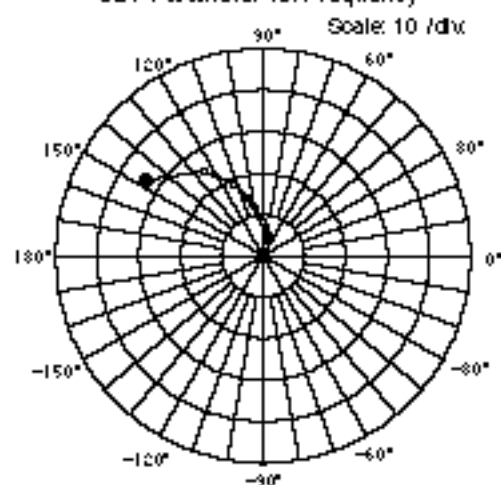
S11 Parameter vs. Frequency

Condition :  $V_{CE} = 3 \text{ V}$ ,  $I_C = 20 \text{ mA}$ 

100 to 2000 MHz (100 MHz step)



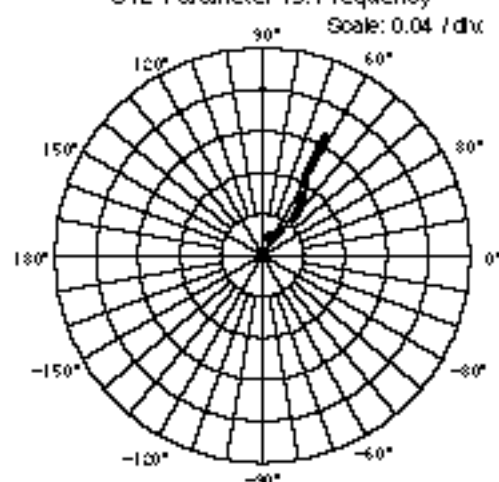
S21 Parameter vs. Frequency

Condition :  $V_{CE} = 3 \text{ V}$ ,  $I_C = 20 \text{ mA}$ 

100 to 2000 MHz (100 MHz step)



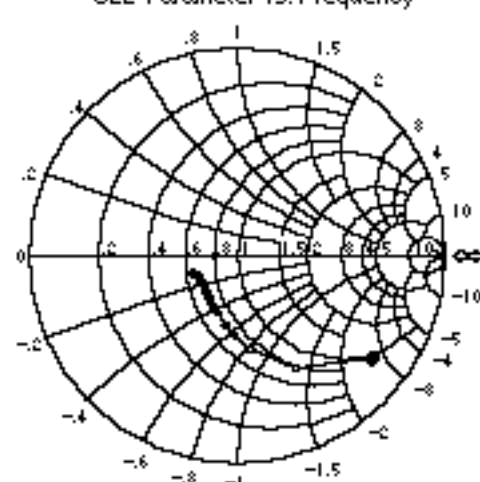
S12 Parameter vs. Frequency

Condition :  $V_{CE} = 3 \text{ V}$ ,  $I_C = 20 \text{ mA}$ 

100 to 2000 MHz (100 MHz step)



S22 Parameter vs. Frequency

Condition :  $V_{CE} = 3 \text{ V}$ ,  $I_C = 20 \text{ mA}$ 

100 to 2000 MHz (100 MHz step)



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## 2SC5545

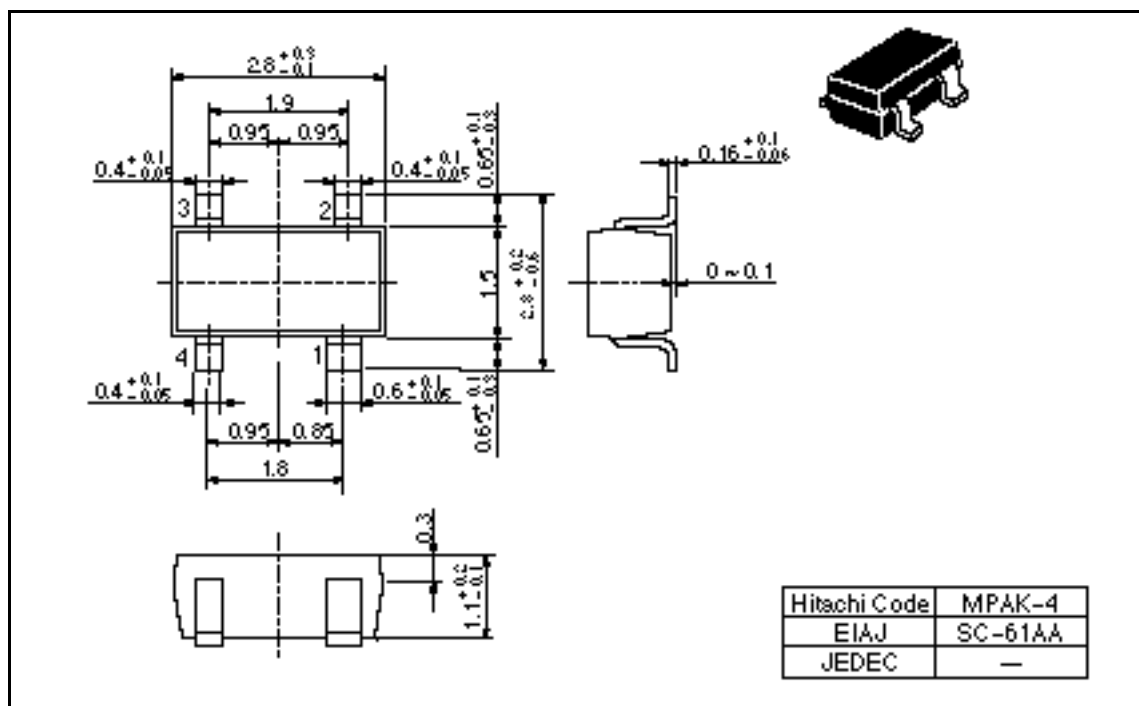
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**Sparameter** ( $V_{CE} = 3V$ ,  $I_C = 20mA$ ,  $Z_o = 50 \Omega$ )

f (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.567	-60.8	34.04	146.8	0.0207	67.3	0.817	-37.3
200	0.539	-102.7	24.61	125.5	0.0329	54.3	0.605	-63.5
300	0.528	-128.1	18.16	113.2	0.0399	50.6	0.463	-80.5
400	0.525	-143.2	14.26	105.5	0.0447	50.3	0.379	-92.4
500	0.518	-153.6	11.65	100.2	0.0495	51.6	0.327	-101.8
600	0.526	-161.2	9.82	96.4	0.0545	53.3	0.293	-109.6
700	0.526	-167.9	8.48	92.9	0.0594	54.8	0.269	-116.2
800	0.528	-172.8	7.46	90.0	0.0639	56.1	0.253	-121.9
900	0.532	-178.3	6.63	87.4	0.0698	57.7	0.242	-127.0
1000	0.535	-178.2	6.00	85.1	0.0741	58.7	0.235	-131.2
1100	0.536	-174.2	5.48	82.9	0.0801	59.5	0.229	-135.1
1200	0.549	-170.6	5.04	81.0	0.0851	60.6	0.225	-139.1
1300	0.546	-167.6	4.67	79.1	0.0901	60.9	0.223	-142.0
1400	0.547	-165.4	4.34	77.4	0.0961	61.5	0.222	-144.7
1500	0.552	-162.4	4.09	75.7	0.102	62.1	0.222	-147.2
1600	0.562	-159.4	3.82	74.0	0.106	62.3	0.223	-149.7
1700	0.561	-157.3	3.62	72.5	0.113	62.5	0.224	-152.3
1800	0.563	-154.8	3.43	70.7	0.118	62.9	0.227	-154.3
1900	0.573	-152.5	3.26	69.2	0.124	62.3	0.229	-155.8
2000	0.577	-150.0	3.13	67.8	0.130	63.0	0.232	-157.6

## Package Dimensions

Unit: mm



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